

产品规格书

Specifcation of products

产品名称:快速单相整流桥

产品型号:MFQ200U12N-H2

浙江世菱半导体有限公司
ZHEJIANG SHILING SEMICONDUCTOR CO.,LTD.

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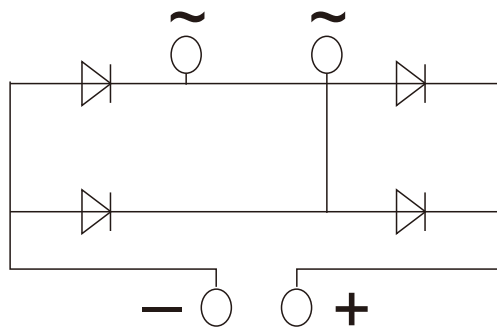
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拟制	审核	核准
林益龙	曹剑龙	宗瑞

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	T _j (°C)	VALUE			UNIT
				Min	Type	Max	
I _O	DC output current	Three-phase full wave rectifying circuit, T _C =100 °C	150		200		A
V _{RRM}	Repetitive peak reverse voltage	V _{RRM} tp=10ms V _{RSM} = V _{DRM} &V _{RRM} +200V	150		1200		V
I _{RRM}	Repetitive peak current	at V _{RRM}	150			10	mA
I _{FSM}	Surge forward current	10ms half sine wave	150			2.24	KA
I ² t	I ² T for fusing coordination	V _R =0.6V _{RRM}				25.0	A ² s*10 ³
V _{FO}	Threshold voltage		150			0.80	V
r _F	Forward slop resistance					1.20	mΩ
V _{FM}	Peak forward voltage	I _{FM} =200A	25		2.3		V
t _{rr}	Reverse Recove ry Tei m	I _F =1A, V _R =30V, di _F /dt=-200A/μs				57	ns
R _{th(j-c)}	Thermal resistance Junction to heatsink	Single side cooled				0.45	°C /W
V _{iso}	Isolation voltage	50Hz, R.M. S, t=1min, I _{iso} : 1mA (max)		3000			V
F _m	Terminal connection torque(M6)				5.0		N·m
	Mounting torque(M5)				4.0		N·m
T _{stg}	Stored temperature			-40		125	°C
W _t	Weight				240		g
Outline							

OUTLINE DRAWING & CIRCUIT DIAGRAM



Rating and Characteristic

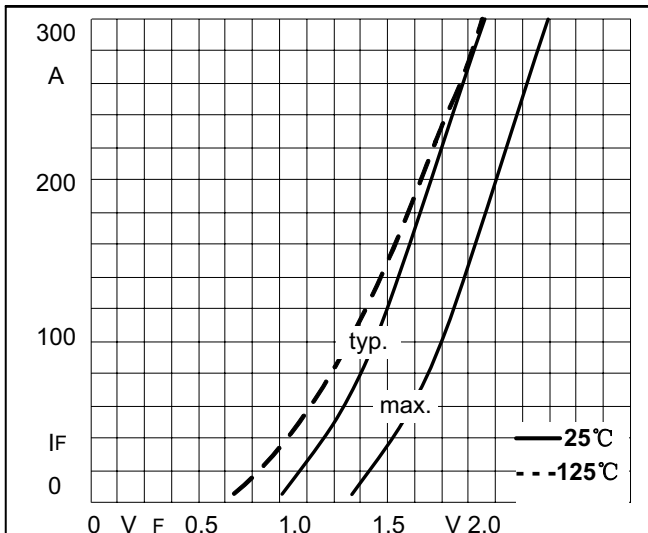


Fig1. Forward Characteristics

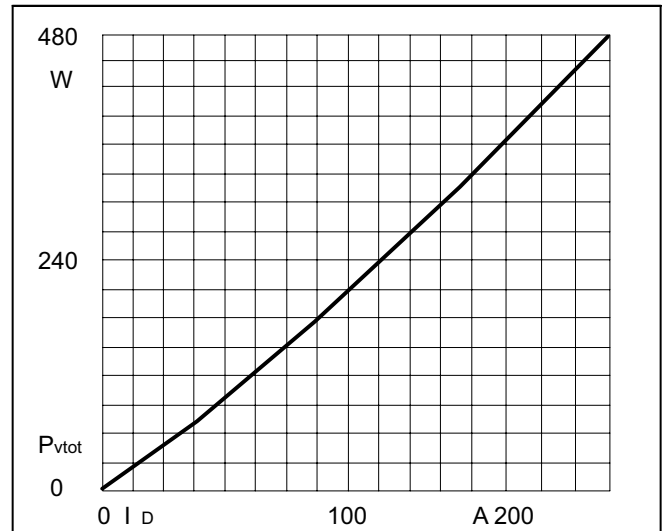


Fig2. Power dissipation

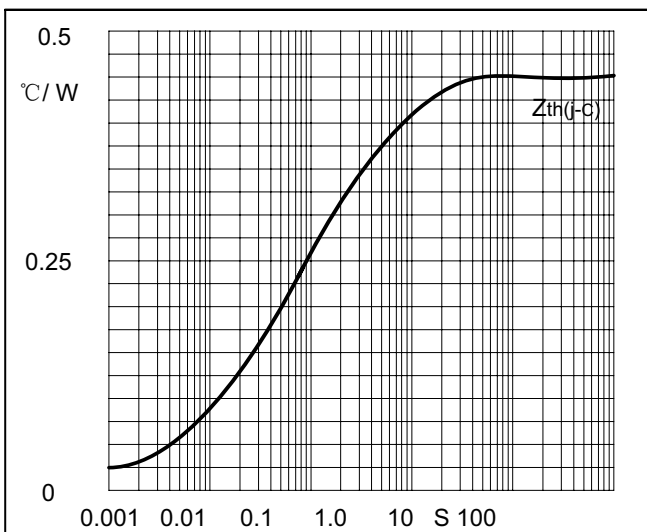


Fig3. Transient thermal impedance

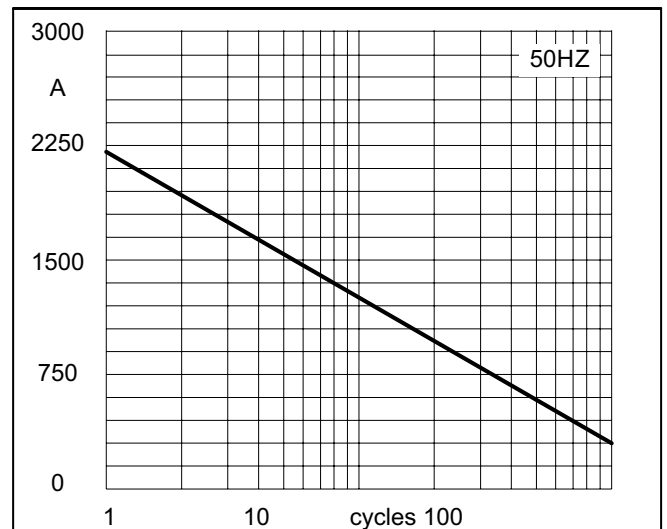


Fig4. Max Non-Repetitive Forward Surge Current

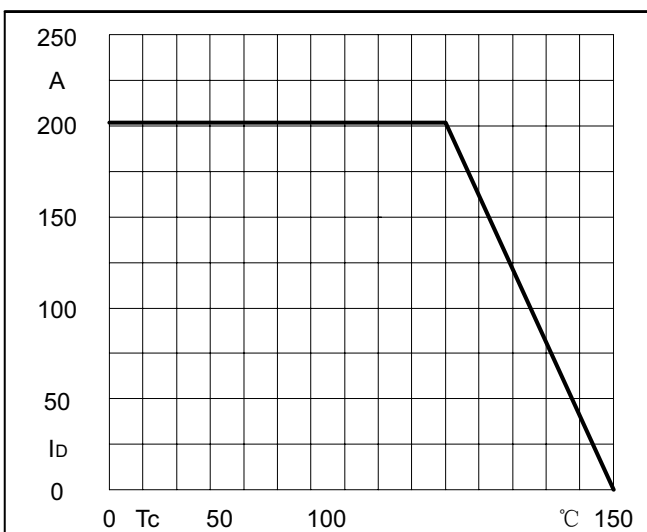


Fig5. Forward Current Derating Curve

Outside Dimension

